

METHODS OF FORMING GATE OXIDE FILMS IN INTEGRATED CIRCUIT
DEVICES USING WET OR DRY OXIDIZATION PROCESSES WITH REDUCED
CHLORIDE

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ABSTRACT

Methods of forming gate oxide films in integrated circuit devices using wet or
dry oxidization processes with a reduced amount of chloride are disclosed. A gate
oxide film is formed on a substrate on an active region adjacent to a trench isolation
region in a first gas atmosphere with a first amount of chloride. The gate oxide film is
10 annealed in a second gas atmosphere including a second amount of chloride that is
greater than the first amount.